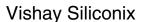
COMPLIANT HALOGEN

FREE





Load Switch with Level-Shift

PRODUCT SUMMARY				
V _{DS2} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
4.5 to 20	0.075 at V _{IN} = 10 V	± 2.3		
	0.120 at V _{IN} = 5.0 V	± 1.9		
	0.145 at V _{IN} = 4.5 V	± 1.7		

FEATURES

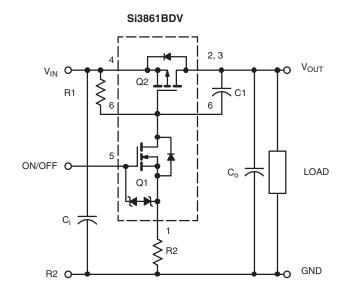
- Halogen-free According to IEC 61249-2-21 Definition
- 4.5 V Rated
- ESD Protected: 3000 V
- 105 mΩ Low R_{DS(on)} TrenchFET[®]
- 4.5 V to 20 V Input
- 1.5 V to 8 V Logic Level Control
- · Low Profile, Small Footprint TSOP-6 Package
- 3000 V ESD Protection On Input Switch, VON/OFF
- Adjustable Slew-Rate
- Compliant to RoHS Directive 2002/95/EC

DESCRIPTION

The Si3861BDV includes a P- and N-Channel MOSFET in a single TSOP-6 package. The low on-resistance P-Channel TrenchFET[®] is tailored for use as a load switch. The N-Channel, with an external resistor, can be used as a level-

shift to drive the P-Channel load-switch. The N-Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si3861DV operates on supply lines from 4.5 to 20 V, and can drive loads up to 2.3 A.

APPLICATION CIRCUITS



	¹⁰ [
					t _f	/	
	8						
	6 -		t _{d(off)}				
Time (µS)	Ĭ			\searrow			
Time	4		t _r			\prec	
						 L_ = 1 A	
	2 -		t _{d(on)}			$I_L = 1 \text{ A}$ $V_{ON/OFF}$ $C_i = 10 \mu$ $C_o = 1 \mu$	= 3 V — F =
	0 L		2 4	4 6	3 8	B 1	0 12
	Ü	•	_		(kΩ)		

Note: For R2 switching variations with other V_{IN}/R1 combinations See Typical Characteristics

COMPONENTS				
R1	Pull-Up Resistor	Typical 10 k Ω to 1 m Ω^*		
R2	Optional Slew-Rate Control	Typical 0 to 100 kΩ*		
C1	Optional Slew-Rate Control	Typical 1000 pF		

Note:

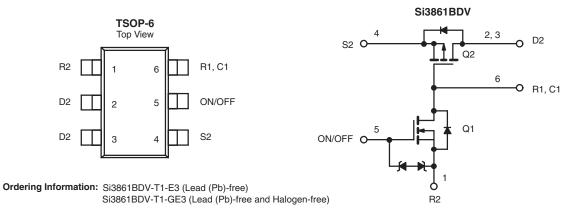
The Si3861BDV is ideally suited for high-side load switching in portable applications. The integrated N-Channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

^{*} Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

Si3861BDV

Vishay Siliconix

FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	Limit	Unit		
Input Voltage		V_{IN}	20	V		
ON/OFF Voltage		V _{ON/OFF}	8	1 V		
Load Current C	Continuous ^{a, b}	1	± 2.3			
Load Current	Pulsed ^{b, c}	'L	± 4	А		
Continuous Intrinsic Diode Conduction ^a		I _S	- 1			
Maximum Power Dissipation ^a		P_{D}	0.83	W		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		
ESD Rating, MIL-STD-883D Human Body Model (100 pf	ESD	3	kV			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient (Continuous Current) ^a	R _{thJA}	120	150	°C/W		
Maximum Junction-to-Foot (Q2)	R _{thJF}	60	80	- C/W		

SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
OFF Characteristics								
Reverse Leakage Current	I _{FL}	V _{IN} = 30 V, V _{ON/OFF} =			1	μΑ		
Diode Forward Voltage	V_{SD}	I _S = - 1 A		- 0.8	- 1	V		
ON Characteristics								
Input Voltage Range	V _{IN}		4.5		20	V		
On-Resistance (P-Channel) at 1 A	R _{DS(on)}	V _{ON/OFF} = 1.5 V, I _D = 1 A	V _{IN} = 10 V		0.060	0.075		
			V _{IN} = 5.0 V		0.096	0.120	Ω	
		V _{IN} = 4.5 V			0.115	0.145		
On-State (P-Channel) Drain-Current	I _{D(on)}	$V_{IN-OUT} \le 0.2 \text{ V}, V_{IN} = 10 \text{ V}, V_{C}$	1			^		
		$V_{IN-OUT} \le 0.3 \text{ V}, V_{IN} = 5 \text{ V}, V_{O}$	1			A		

Notes:

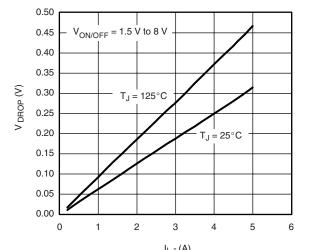
- a. Surface Mounted on FR4 board.
- b. V_{IN} = 12 V, $V_{ON/OFF}$ = 8 V, T_A = 25 °C. c. Pulse test: pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

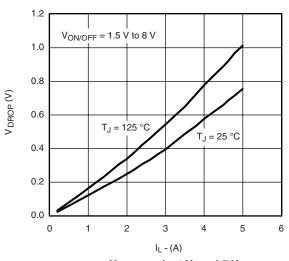


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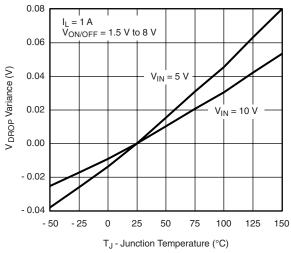
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



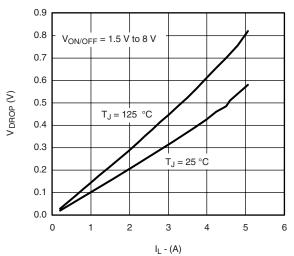
 V_{DROP} vs. I_L at V_{IN} = 10 V



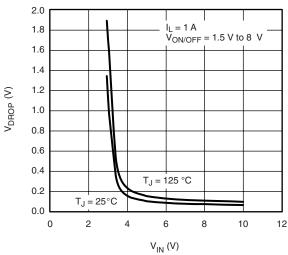
 V_{DROP} vs. I_L at V_{IN} = 4.5 V



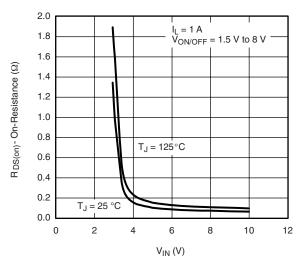
VDROP Variance vs. Junction Temperature



 V_{DROP} vs. I_L at $V_{IN} = 5$ V



 V_{DROP} vs. V_{IN} at = 1 A

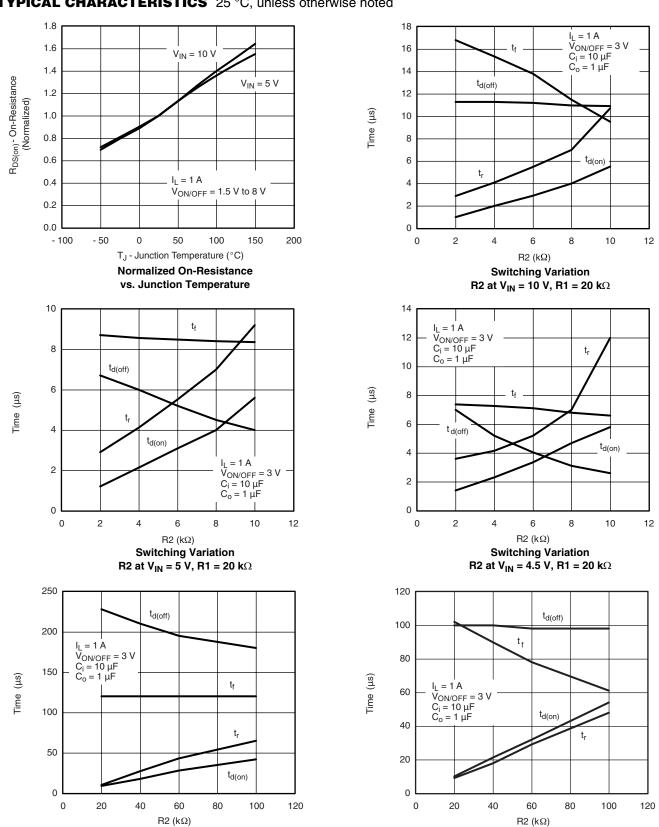


On-Resistance vs. Input Voltage

Si3861BDV

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Switching Variation

R2 at V_{IN} = 10 V, R1 = 300 k Ω

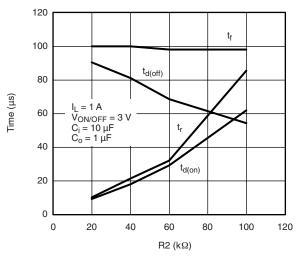
Switching Variation

R2 at V_{IN} = 5 V, R1 = 300 k Ω

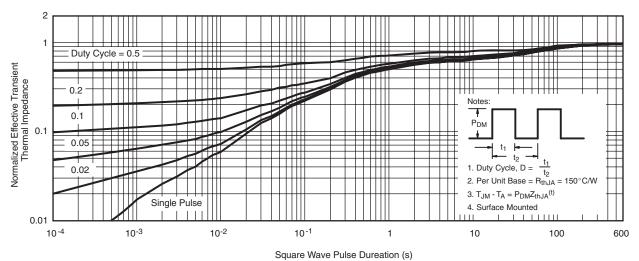


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Switching Variation R2 at V_{IN} = 4.5 V, R1 = 300 k Ω



Normalized Thermal Transient Impedance, Junction-to-Ambient

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